

AMENDMENT TO THE SPECIFICATION

At page 7, kindly replace the paragraph at lines 9-11 with the following substitute paragraph:

A₁
In an embodiment of the invention transferring the image further comprises forming a reduced critical dimension bilayer resist image. Such a process is described in co-pending application Attorney Docket Number 0140/00268 09/902,727 which was published as Patent Application Publication Number US 2003/0017711.

At page 8, following line 7, kindly insert the following paragraph:

A₂
An embodiment of the present invention further comprises forming circuit element materials in the circuit image. In an embodiment circuit element materials comprise materials selected from the group consisting of dielectric, conductor, semiconductor, and doped semiconductor materials.